Product data sheet

1. General description

Dual ultrafast power diodes in a TO3PF plastic package.

2. Features and benefits

- · Very low on-state loss
- · Reduces switching losses in associated MOSFET or IGBT
- Low leakage current
- Isolated plastic package

3. Applications

- Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 101 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	15	Α
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 101 °C$; Square-ware pulse	-	-	30	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	-	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	-	-	165	Α
Static charac	teristics					
V _F	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.17	1.4	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1	-	V
Dynamic cha	racteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	38	-	ns
		I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 25 °C; <u>Fig. 7</u>	-	67	-	ns
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$	-	106	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb O 👝 O	A1 A2
2	K	cathode		
3	A2	anode 2	0 0	K sym125
mb	mb	mounting base	TO3PF	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYV415J-600P	TO3PF	Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack'	TO3PF		

7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 101 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	15	Α
I _{O(AV)}	average output current	δ = 0.5 ; T _h ≤ 90 °C; square-wave pulse; both diodes conducting	-	30	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _h ≤ 101 °C; Squareware pulse	-	30	Α
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>	-	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	-	165	Α
T _{stg}	storage temperature		-65	175	°C
T _j	junction temperature		-	175	°C

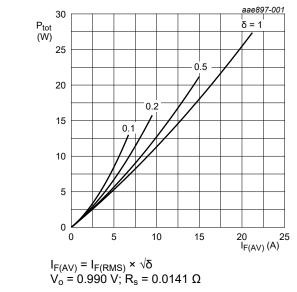


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

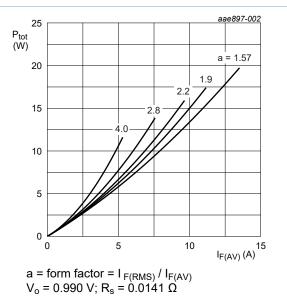


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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Dual ultrafast power diode

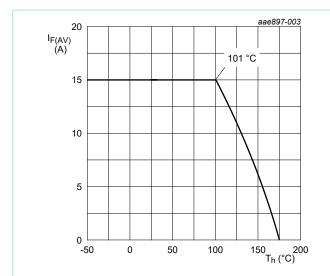


Fig. 3. Average forward current as a function of heatsink temperature; maximum values; per diode

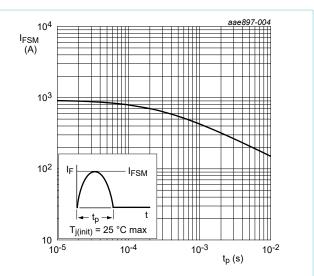


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; per diode; Fig. 5	-	2.9	3.5	K/W
		with heatsink compound; both diodes conducting	-	1.6	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W

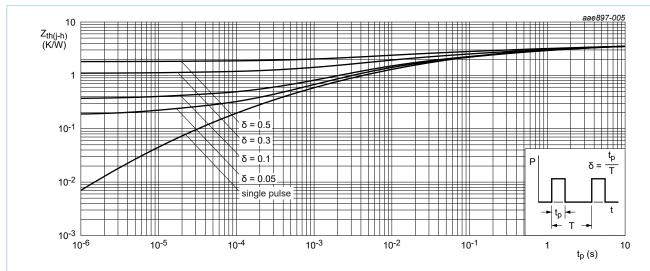
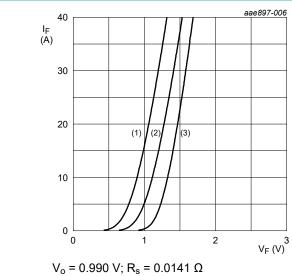


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values; per diode

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.17	1.4	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	500	μΑ
Dynamic ch	naracteristics					_
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	38	-	ns
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	67	-	ns
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 \text{ °C}; Fig. 7$	-	106	-	ns
I _{RM}	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	9.8	-	А
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; \frac{\text{Fig. } 7}{\text{C}}$	-	16	-	А
Q _r	recovered charge	$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	329	-	nC
		I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _i = 125 °C; <u>Fig. 7</u>	-	876	-	nC



(1) $T_j = 150 \,^{\circ}\text{C}$; typical values (2) $T_j = 150 \,^{\circ}\text{C}$; maximum values (3) $T_j = 25 \,^{\circ}\text{C}$; maximum values



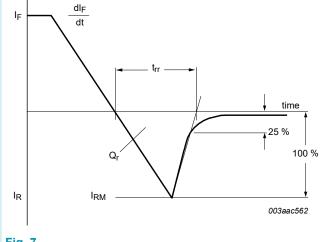
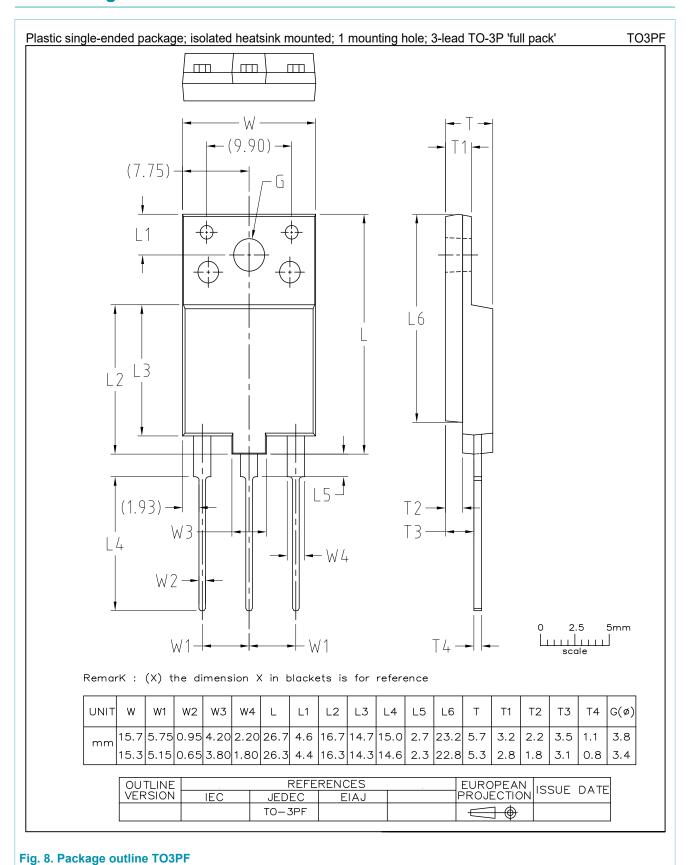


Fig. 7.

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10. Package outline

BYV415J-600P



11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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